

A cross-sectional view of a semiconductor device. A central structure 10 is formed on a substrate 11. The structure 10 includes a central layer 12, a base layer 14, and a bottom layer 16. The base layer 14 is flanked by regions 18 and 18A. The bottom layer 16 is flanked by regions 20 and 22. The substrate 11 is flanked by regions 15 and 15A.

Figure 1

(Prior Art)

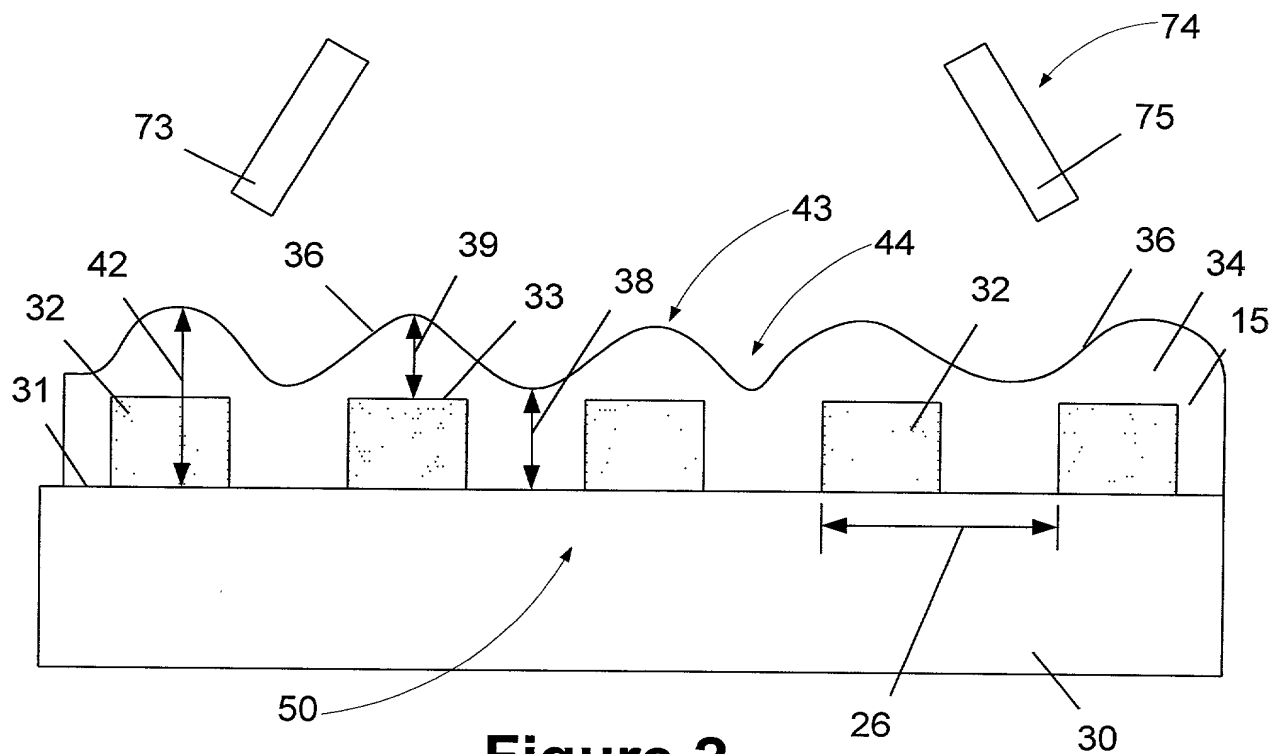


Figure 2

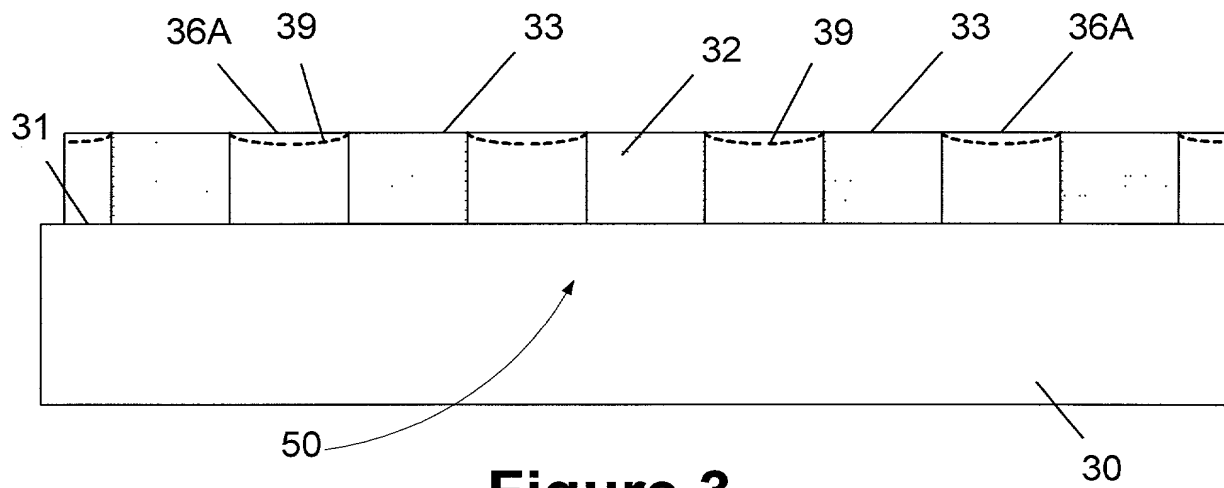


Figure 3

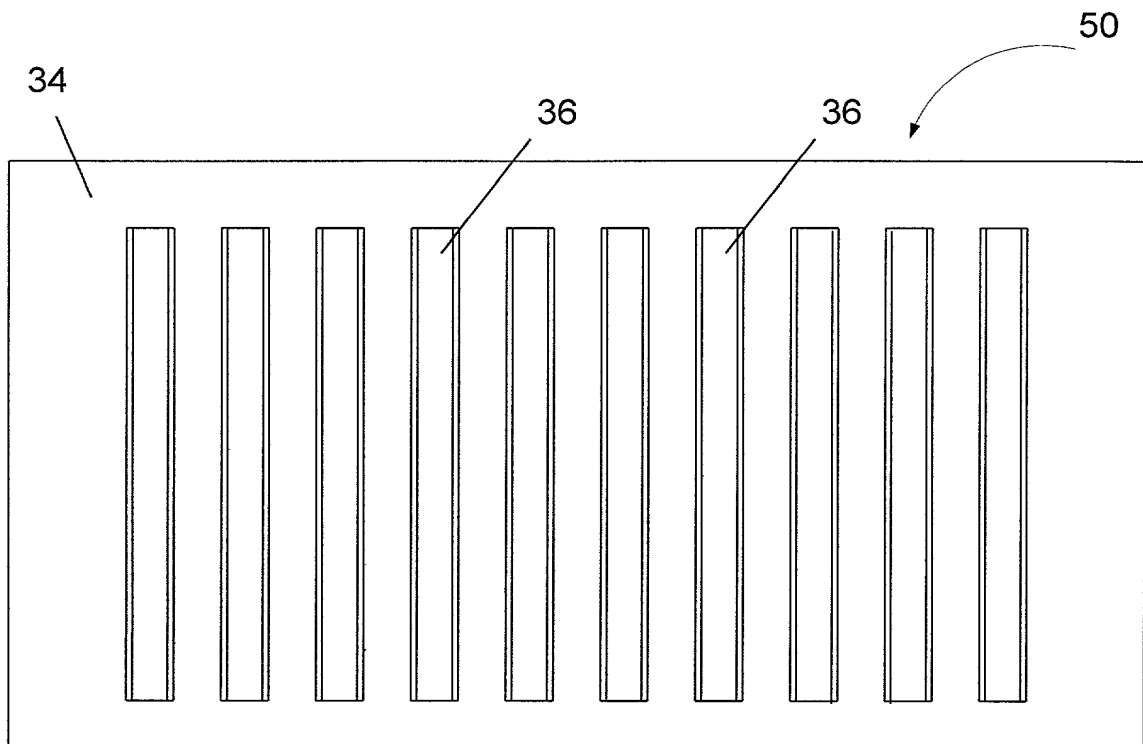


Figure 4

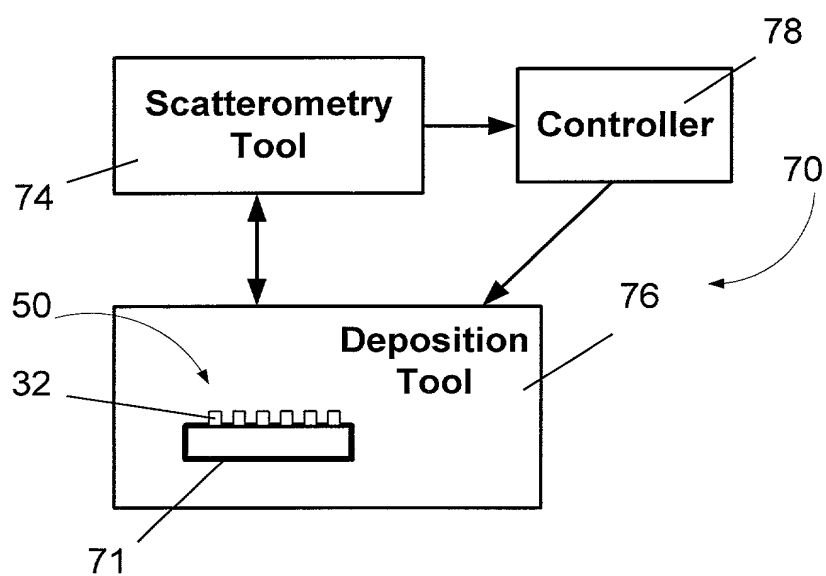


Figure 5